

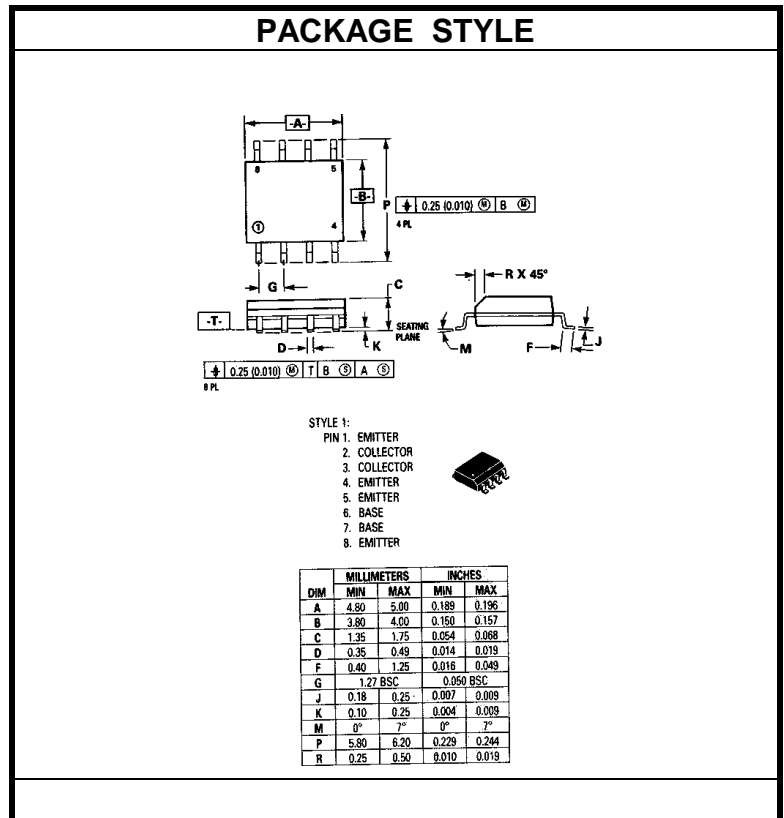
NPN SILICON RF TRANSISTOR

DESCRIPTION:

The **ASI MRF3866** is Designed for General Purpose Amplifier and Oscillator Applications.

MAXIMUM RATINGS

I_C	400 mA
V_{CE}	30 V
V_{CB}	55 V
V_{EB}	3.5 V
P_{DISS}	1.0 W @ $T_C = 100\text{ }^\circ\text{C}$
T_J	-55 $^\circ\text{C}$ to +150 $^\circ\text{C}$
T_{STG}	-55 $^\circ\text{C}$ to +150 $^\circ\text{C}$
θ_{JC}	125 $^\circ\text{C/W}$


CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 5.0\text{ mA}$		30			V
BV_{CBO}	$I_C = 100\text{ }\mu\text{A}$		55			V
BV_{EBO}	$I_E = 100\text{ }\mu\text{A}$		3.5			V
I_{CEO}	$V_{CB} = 28\text{ V}$				20	μA
h_{FE}	$V_{CE} = 5.0\text{ V}$	$I_C = 360\text{ mA}$	5.0			---
	$V_{CE} = 5.0\text{ V}$	$I_C = 50\text{ mA}$	10		200	
$V_{CE(sat)}$	$I_C = 100\text{ mA}$	$I_B = 20\text{ mA}$			250	mV
C_{OB}	$V_{CB} = 30\text{ V}$	$f = 1.0\text{ MHz}$			3.0	pF
f_t	$V_{CE} = 15\text{ V}$	$I_C = 50\text{ mA}$		800		MHz